

CSCI 4974 / 6974

Hardware Reverse Engineering

Lecture 4: CMOS layout

Inkscape

- Vector graphics editor
- Very useful for visualizing VLSI layout
- Demo
- Download today's examples

Materials

- Silicon
 - Undoped
 - P-type
 - N-type
 - Polycrystalline
- Insulators
 - Usually SiO_2
 - Sometimes low-k
- Metal
 - Multiple layers
 - Numbered in order

Color-coding convention

- Based on scheme used in Mead & Conway
- Extended for multilevel metallization

P-type doping

Via

M3

N-type doping

M1

M4

Poly

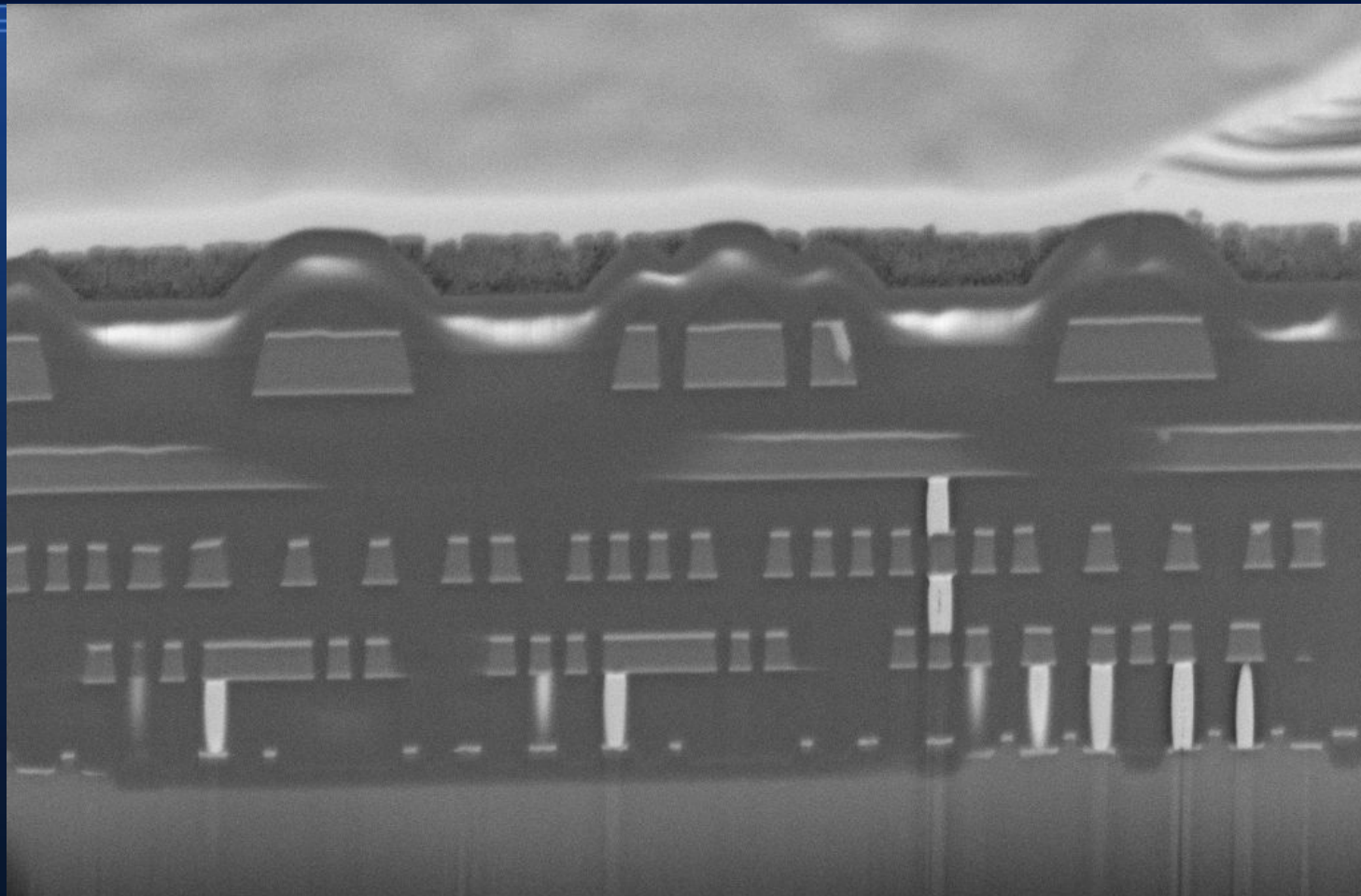
M2

Schematic cross section

Overglass, bond pads, etc



Actual cross section (XC2C32A)



Mag = 15.00 K X 1 μ m
WD = 5.3 mm
Pixel Size = 19.5 nm

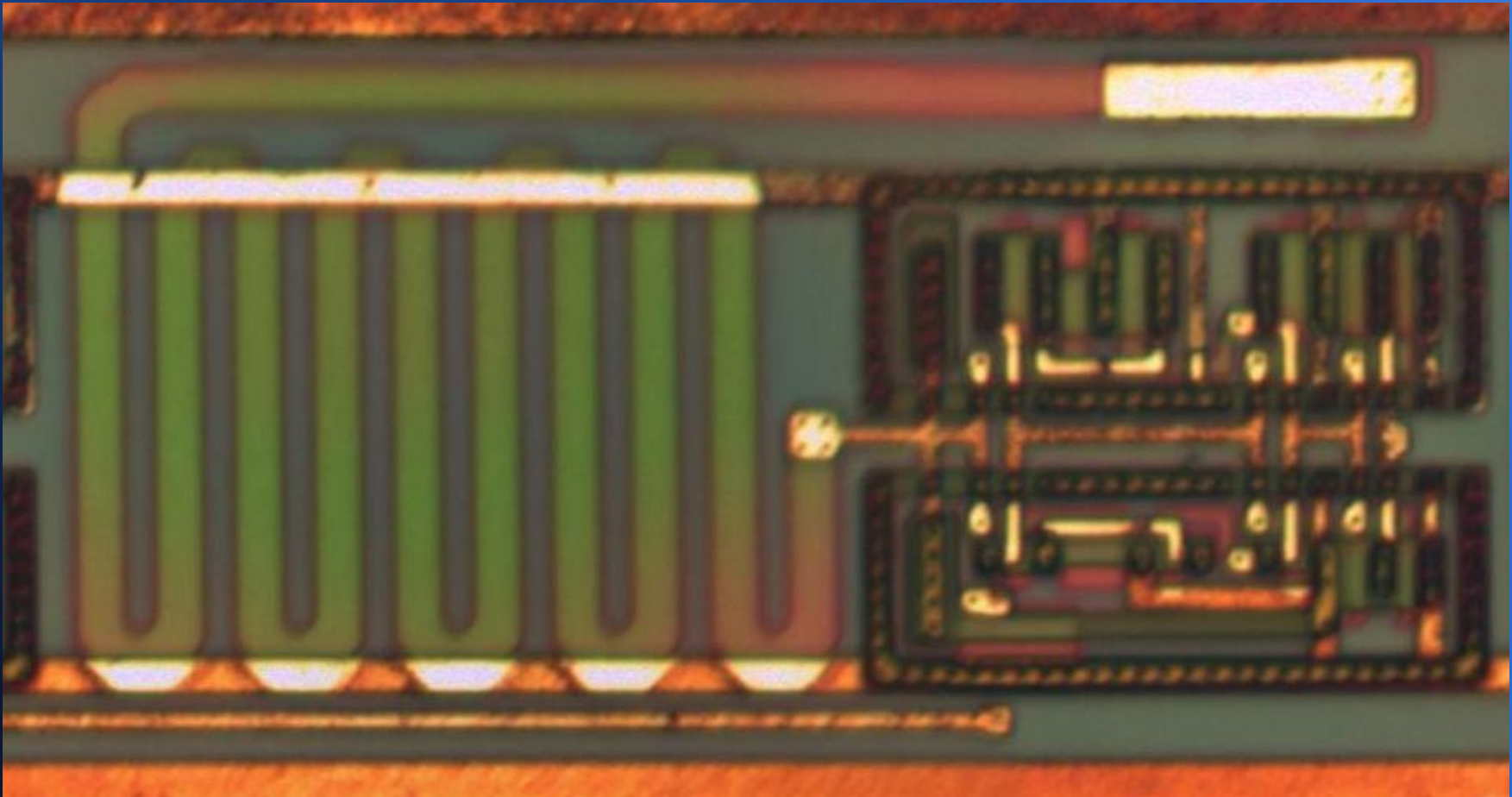
EHT = 5.00 kV
FIB Probe = 30KV:500 pA

Signal A = ESB FIB Lock Mags = Yes
Date :28 Jan 2014 Time :16:04:02

Poly resistor

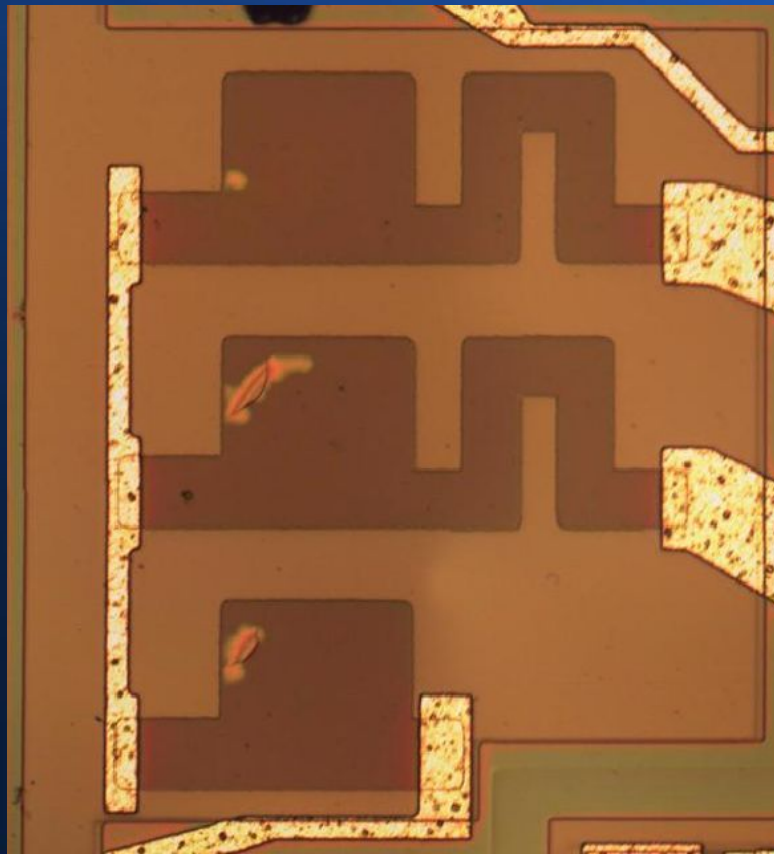


Actual poly resistor



Laser-trimmed film resistor

- Typically only seen in precision analog

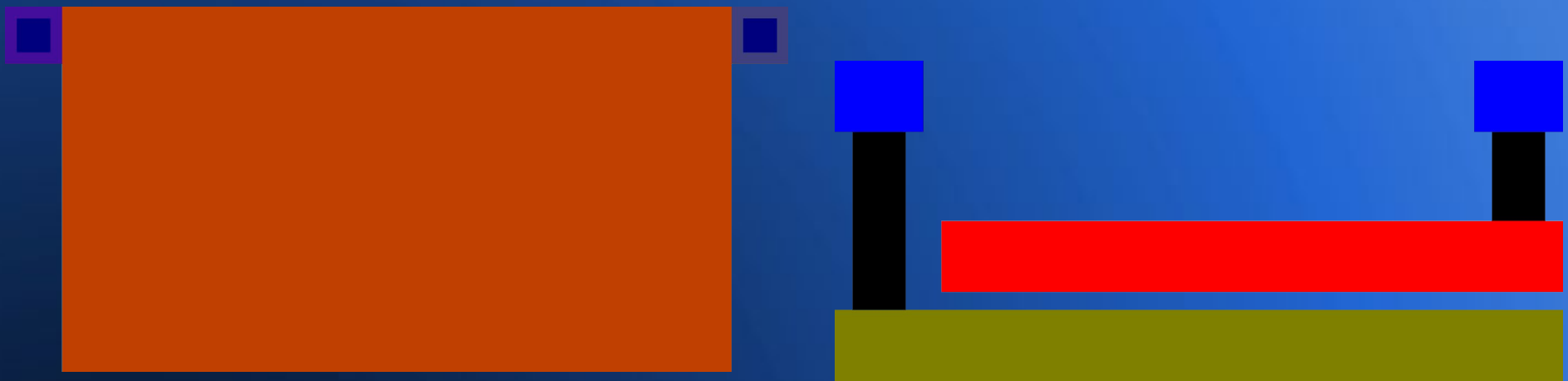


MIM capacitor

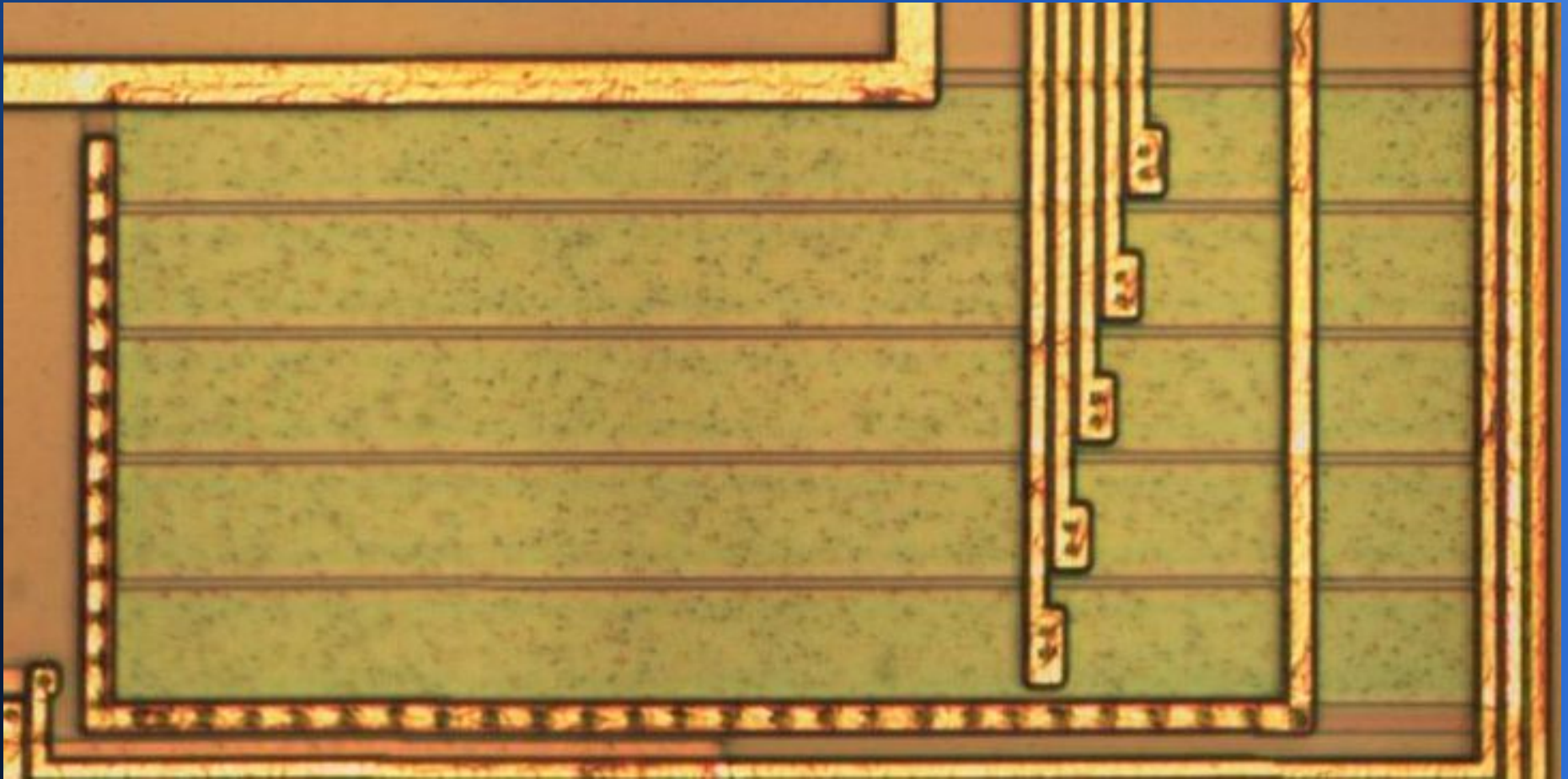
- Metal-Insulator-Metal



Poly (MOS) capacitor



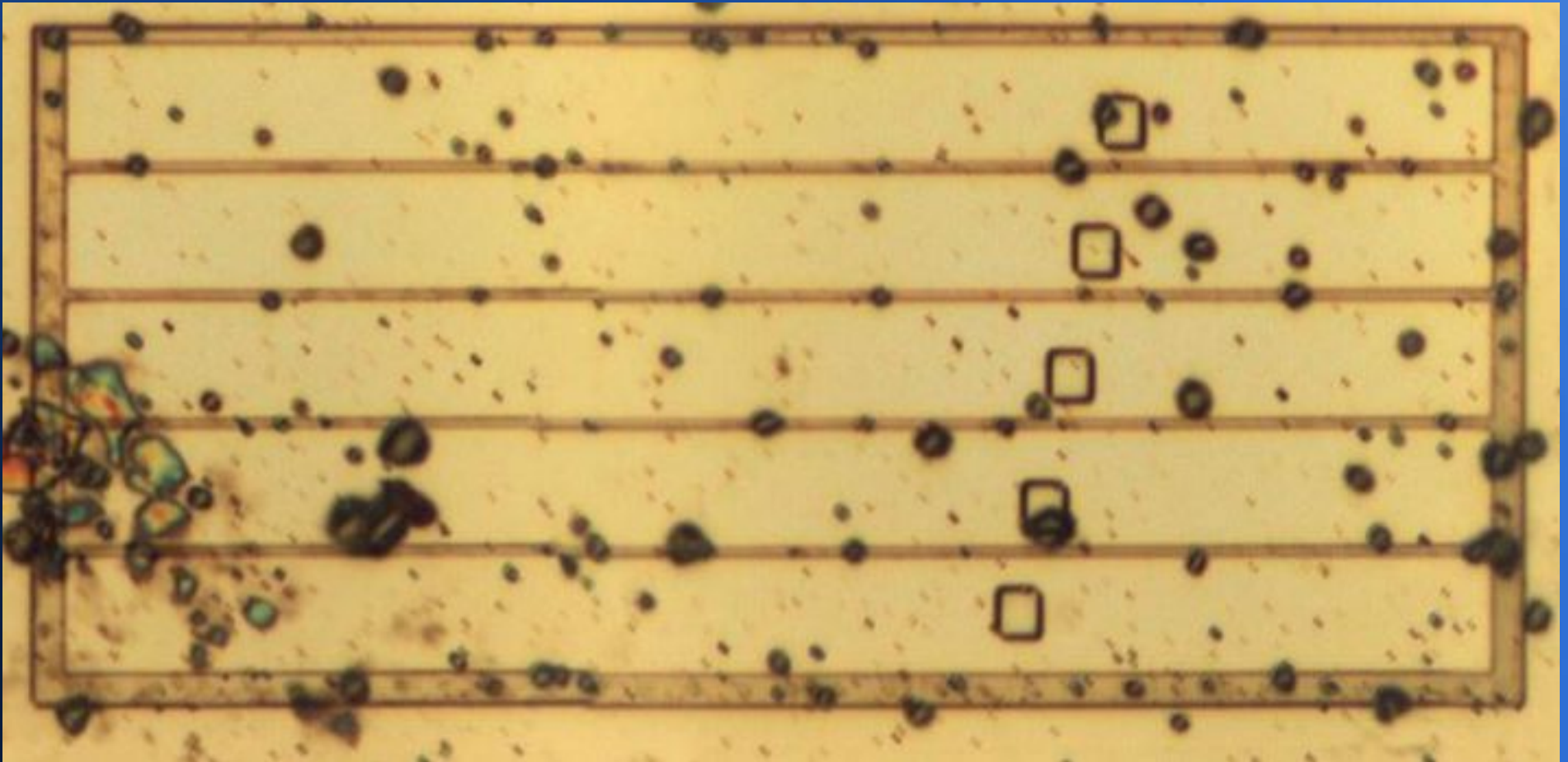
Actual MOS cap (24C02): M1



Actual MOS cap: Poly



Actual MOS cap: Implant



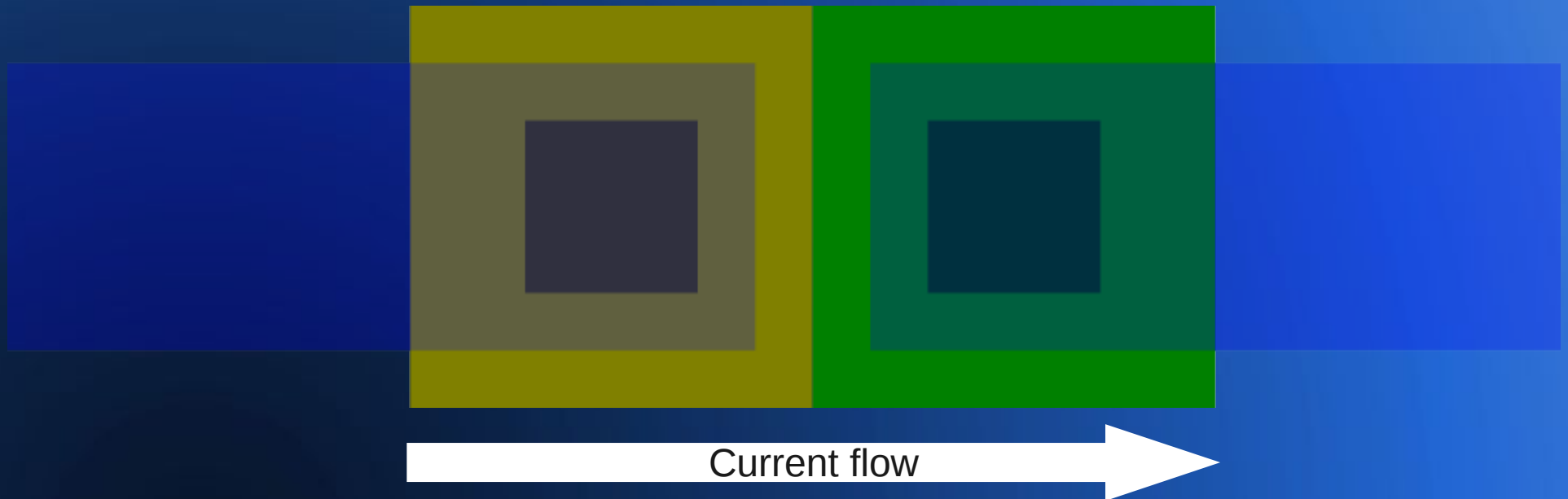
Semiconductor doping

- Semiconductors have few free charge carriers
- Add trace amounts of materials with
 - Extra valence electrons (N-type): P, As
 - Holes in the shell (P-type): B
- Greatly increases conductivity

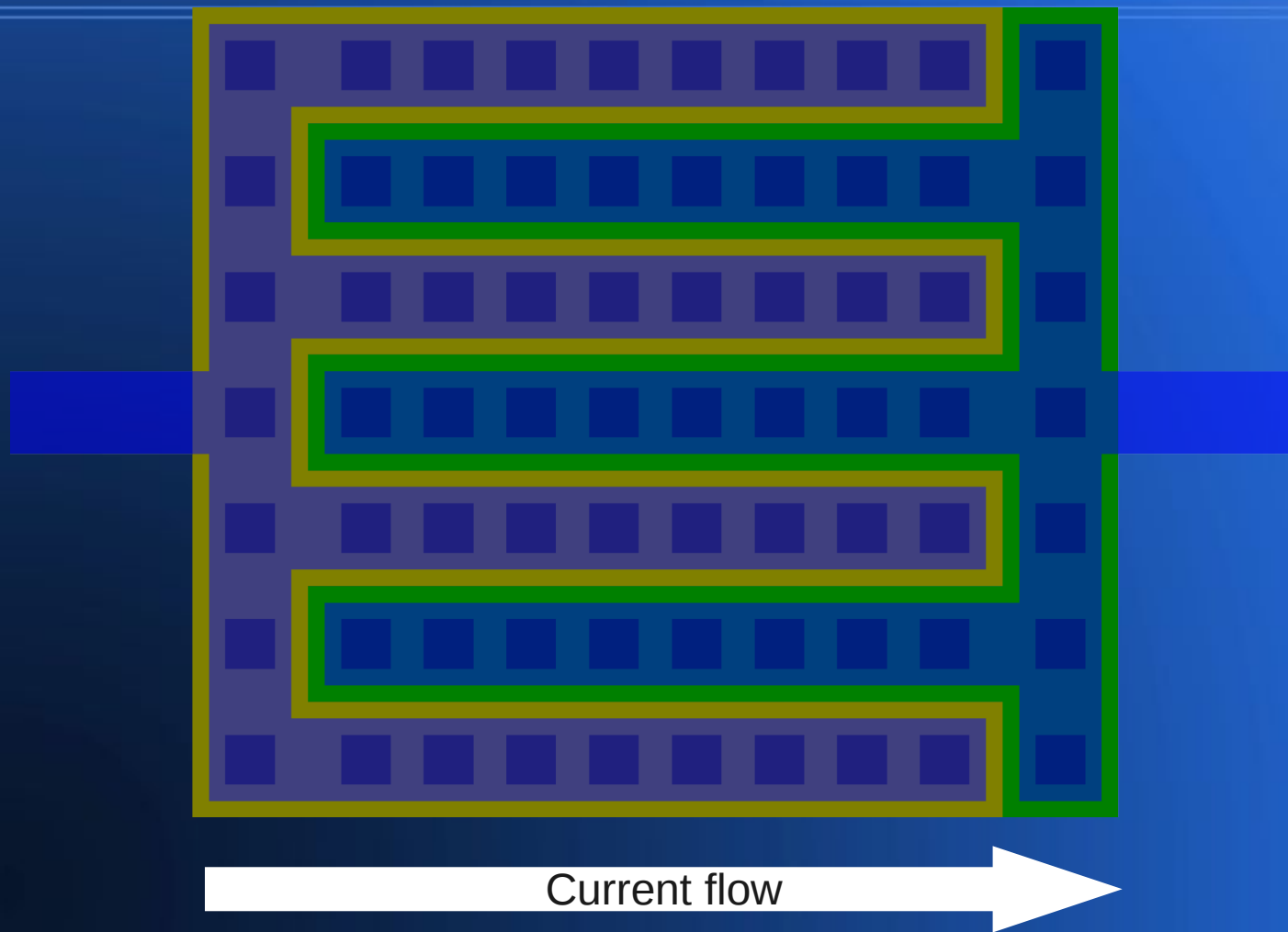
P-N junctions

- Forward bias (P-type higher voltage)
 - Charges pulled across junction
 - Current flows freely
- Reverse bias (P-type lower)
 - Charges pulled away from junction
 - No current flows

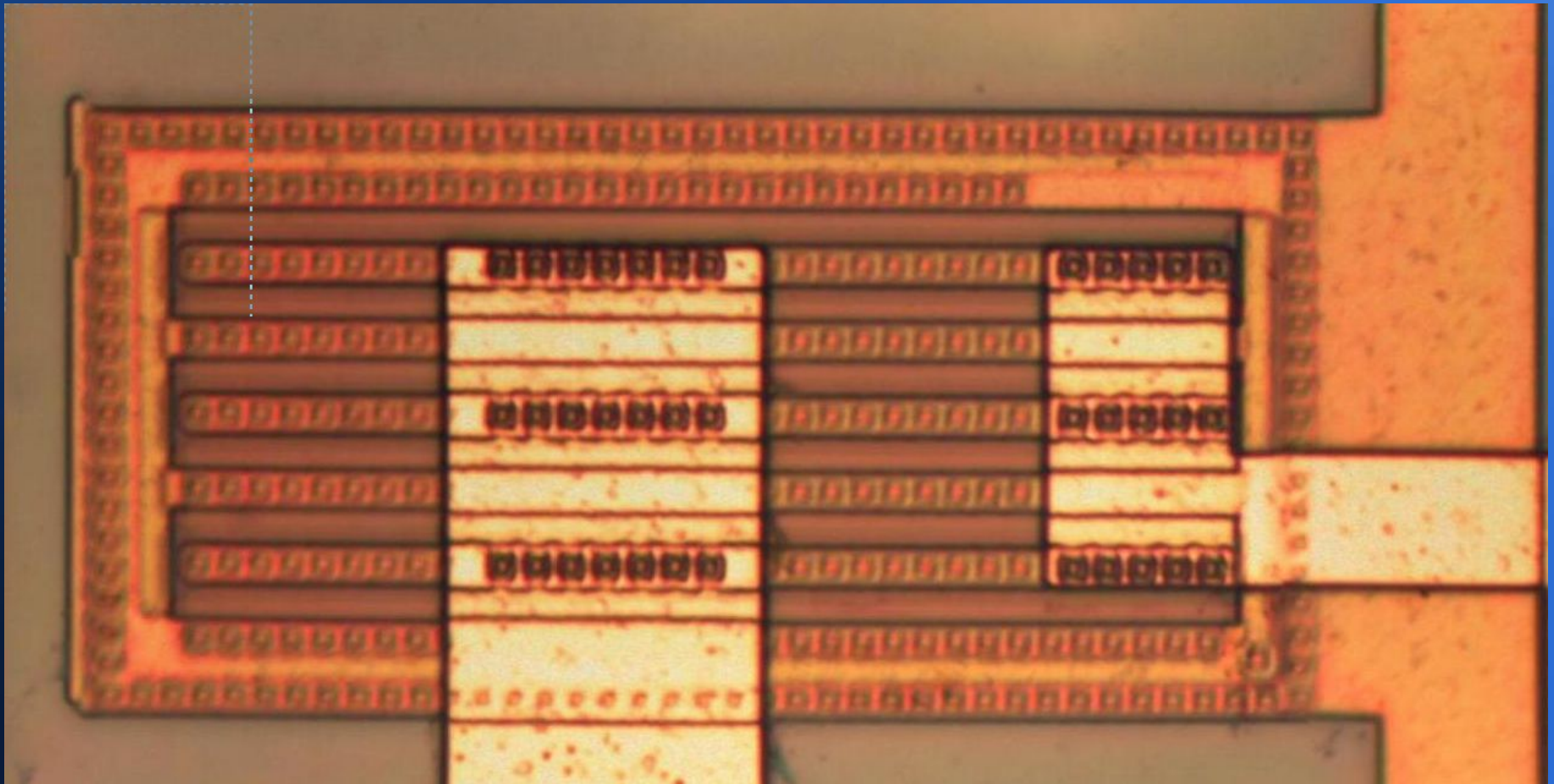
Small-signal diode



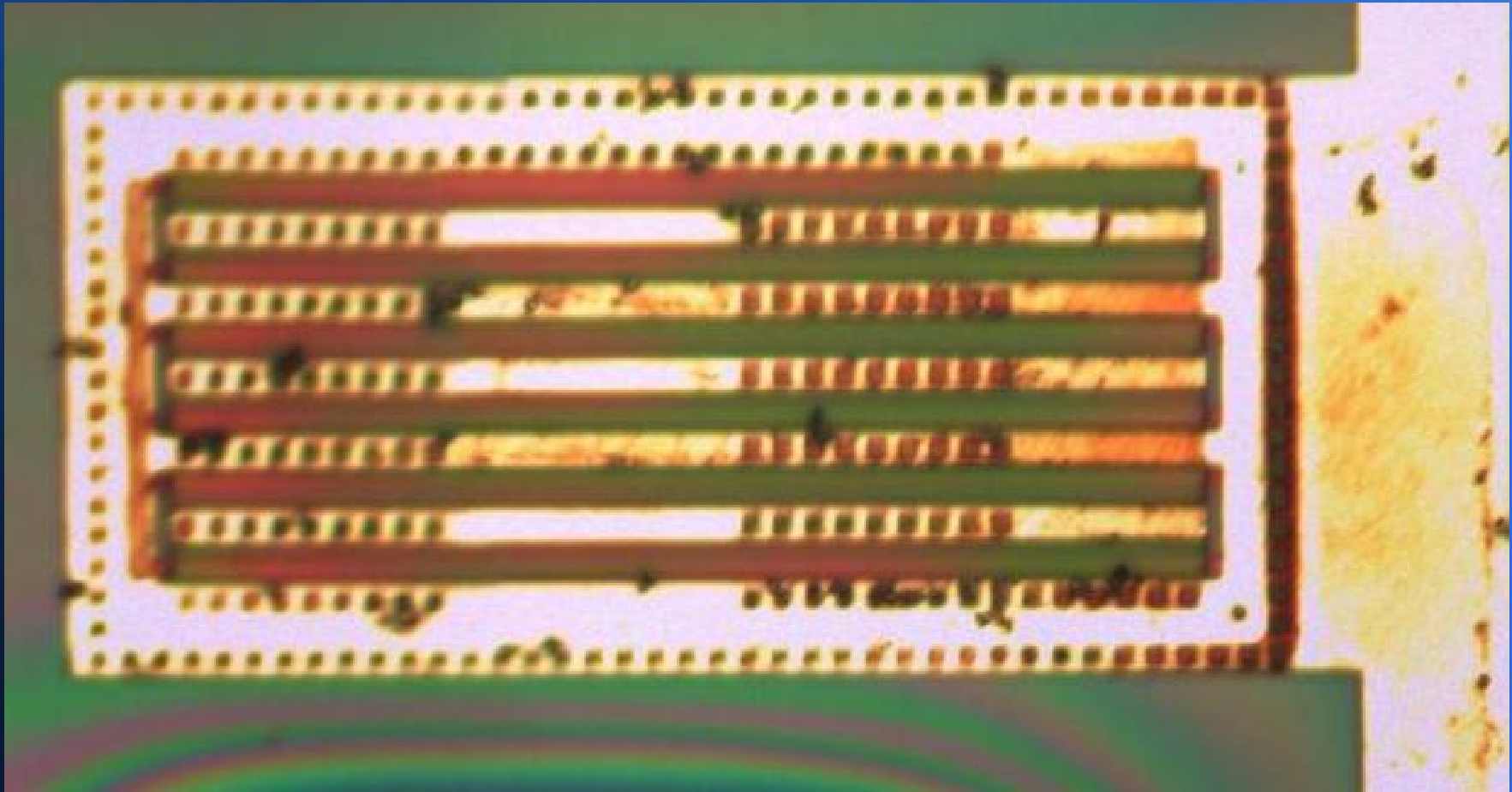
High-current diode



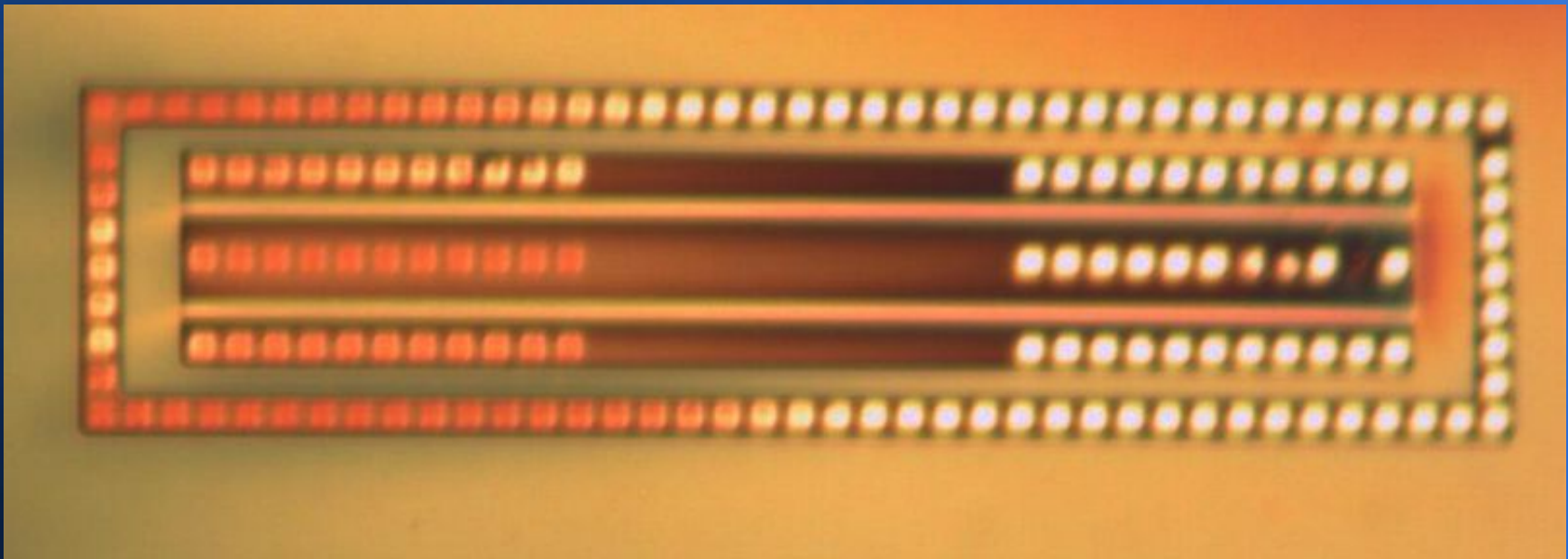
Actual diode (SecurID 600): M2



Actual diode: M1

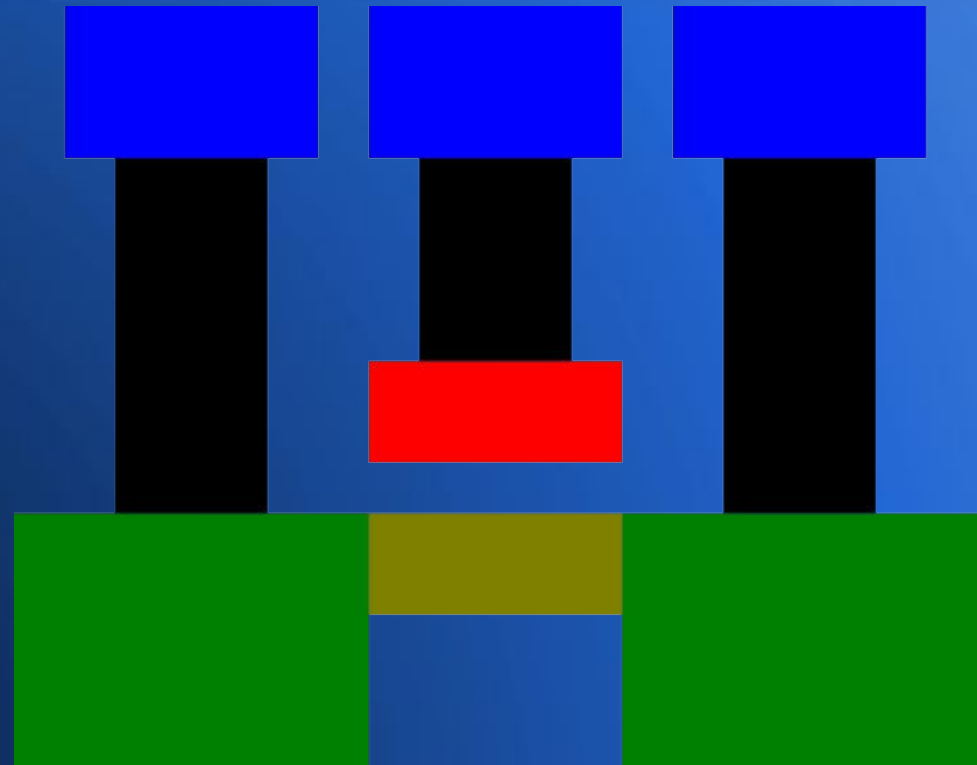
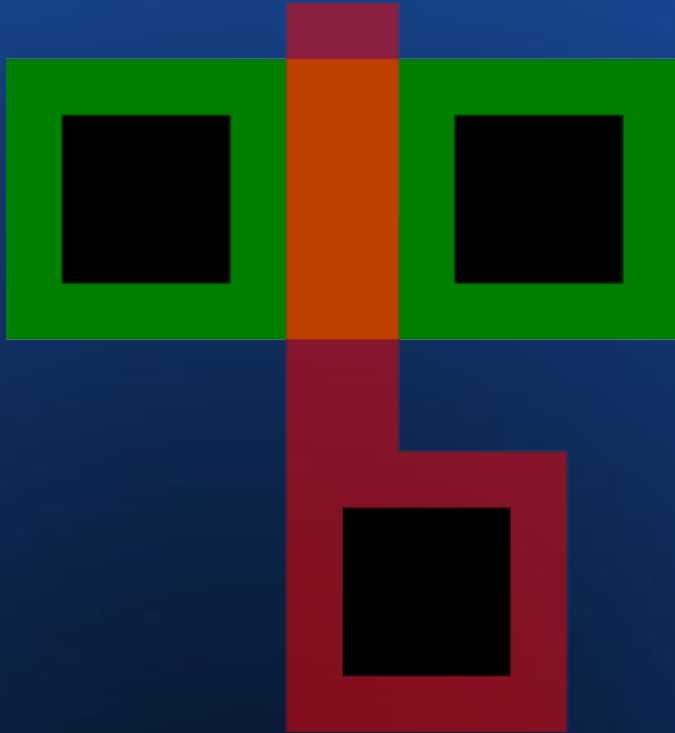


Actual diode: Implant

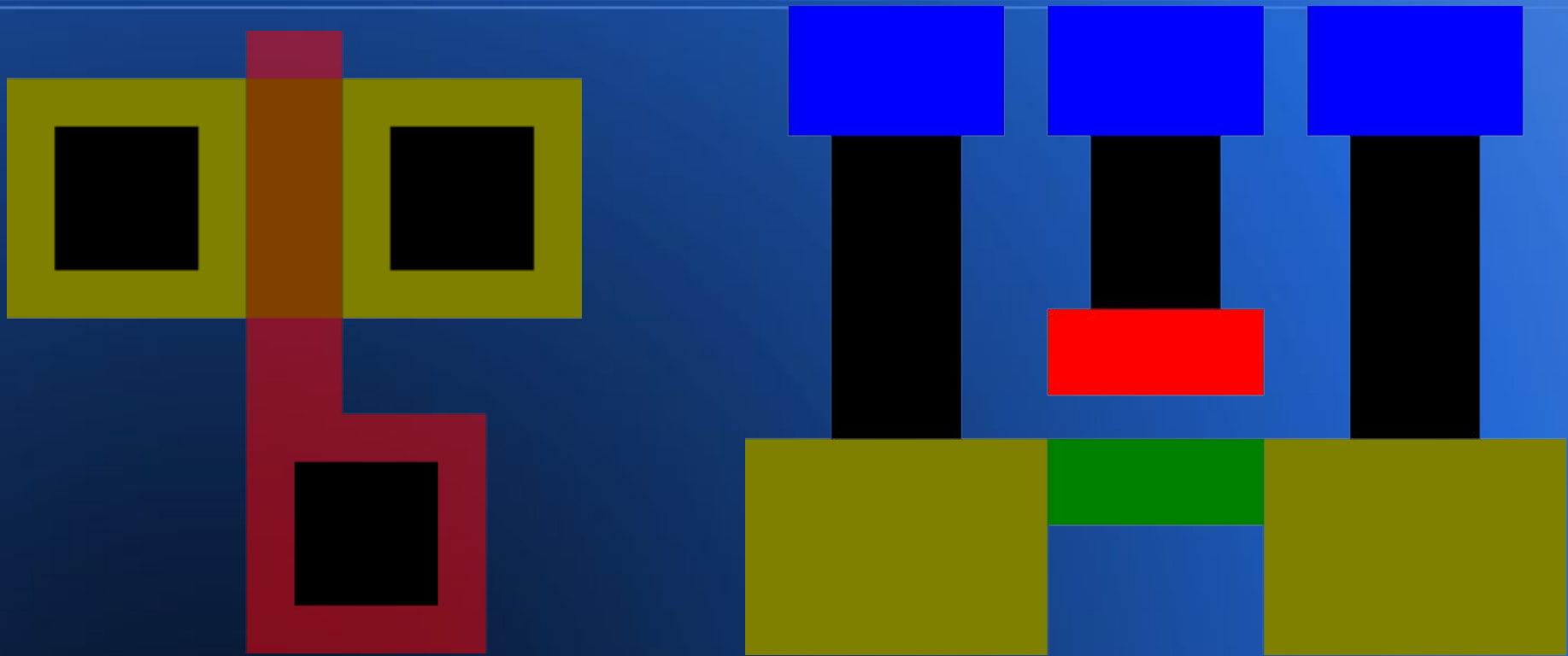


Not same diode as first two pics, that one was damaged during sample prep :(

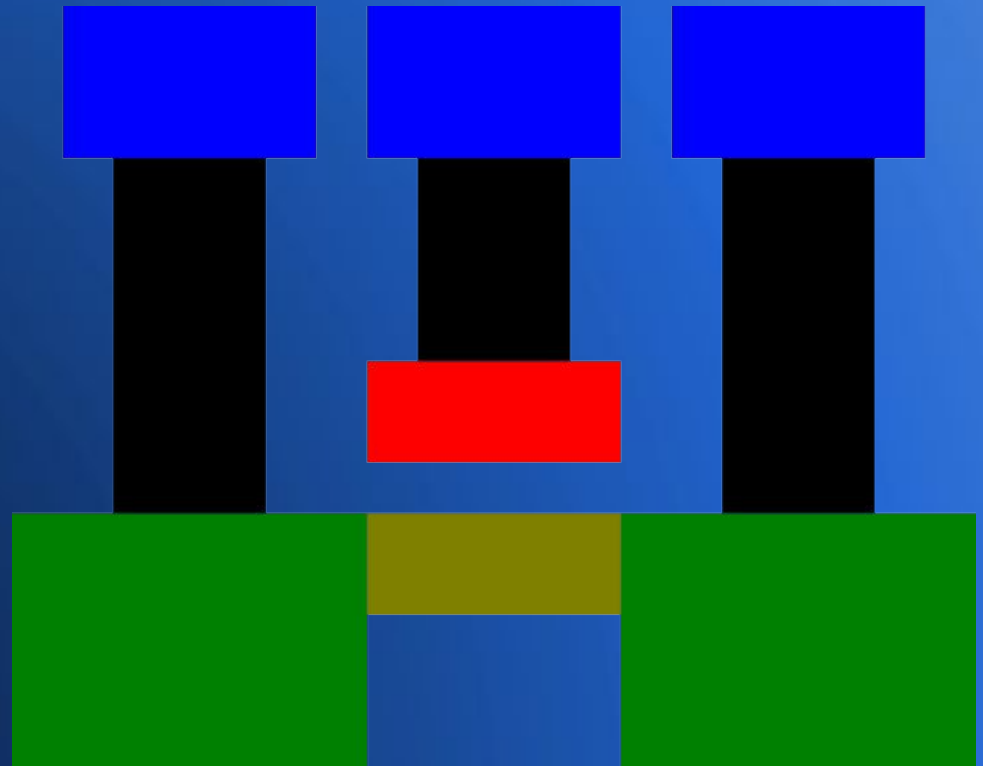
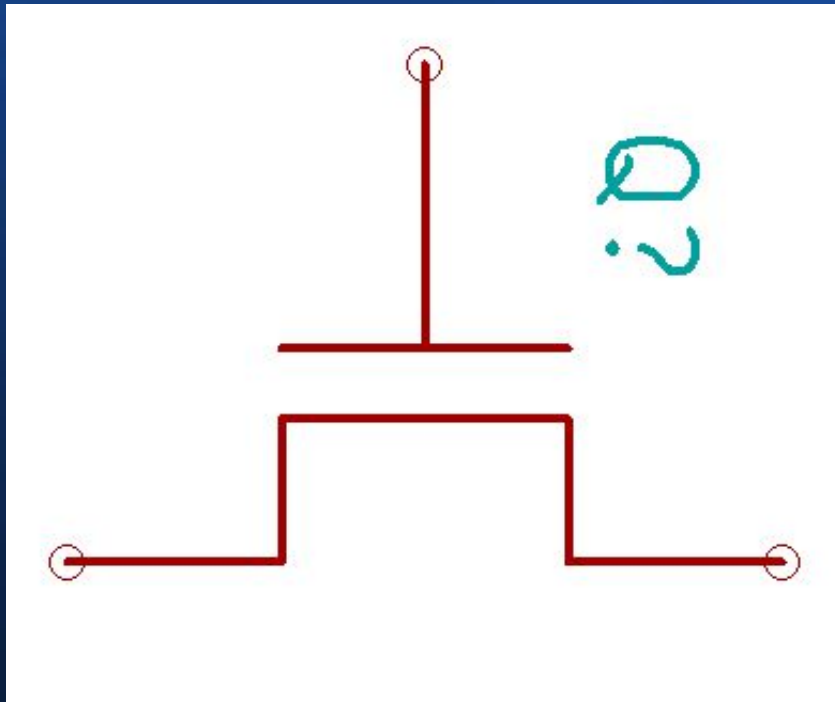
N-channel MOSFET



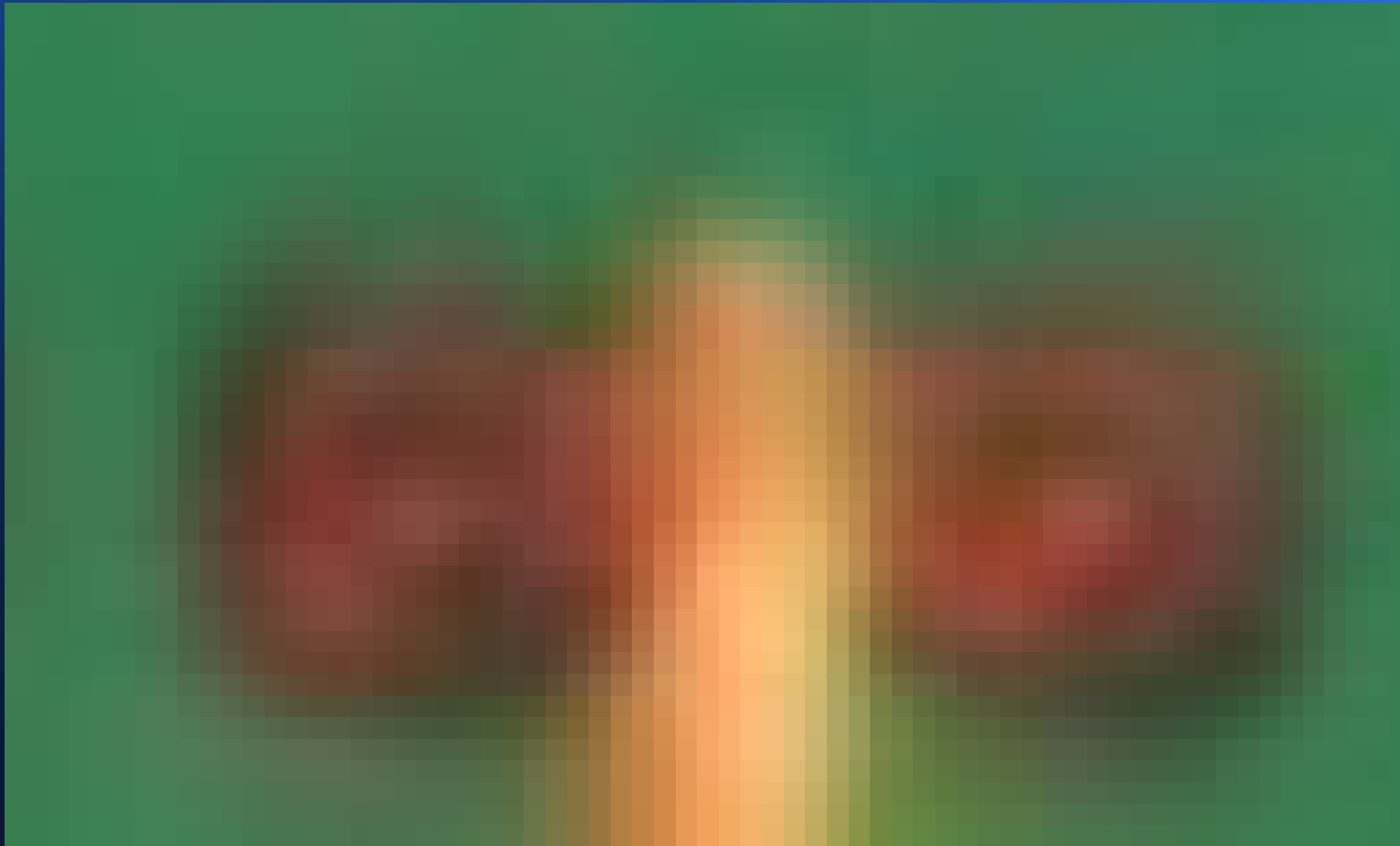
P-channel MOSFET



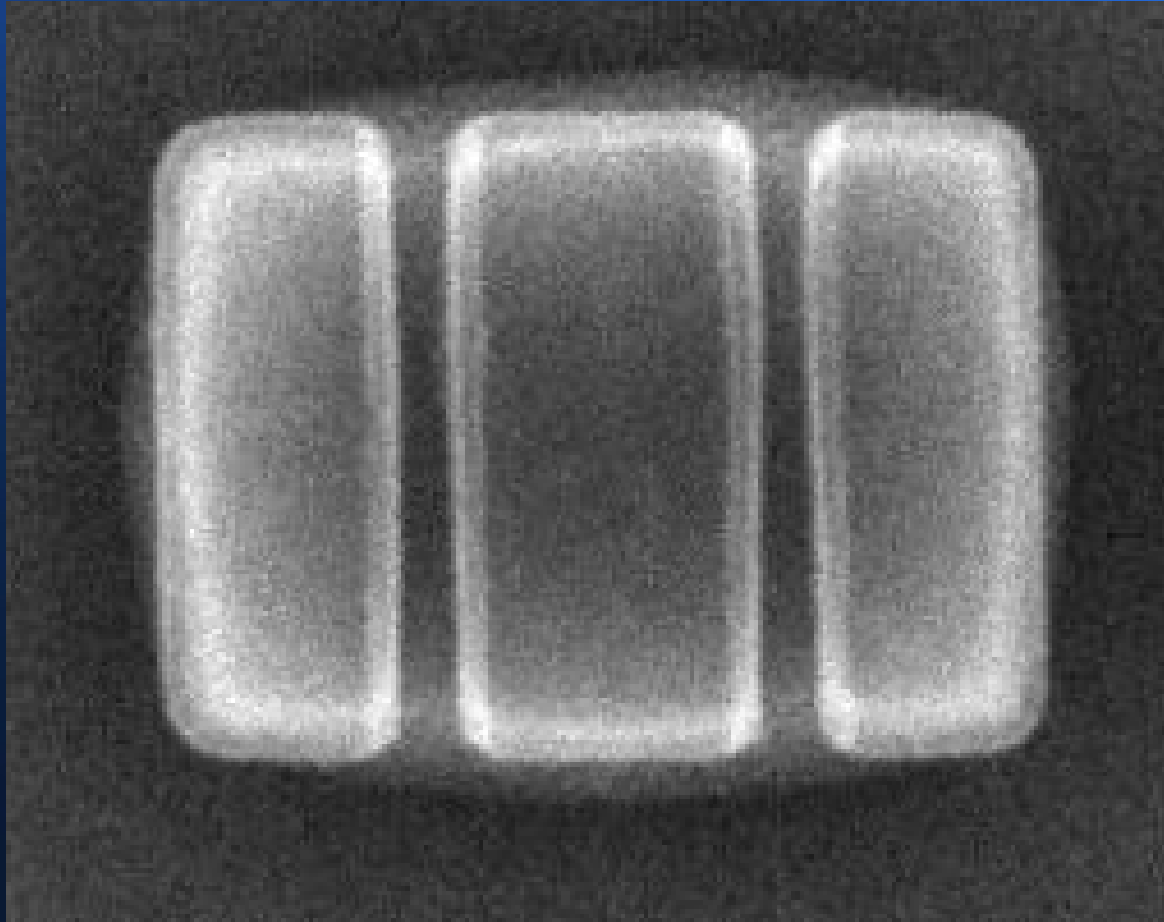
Schematic symbols



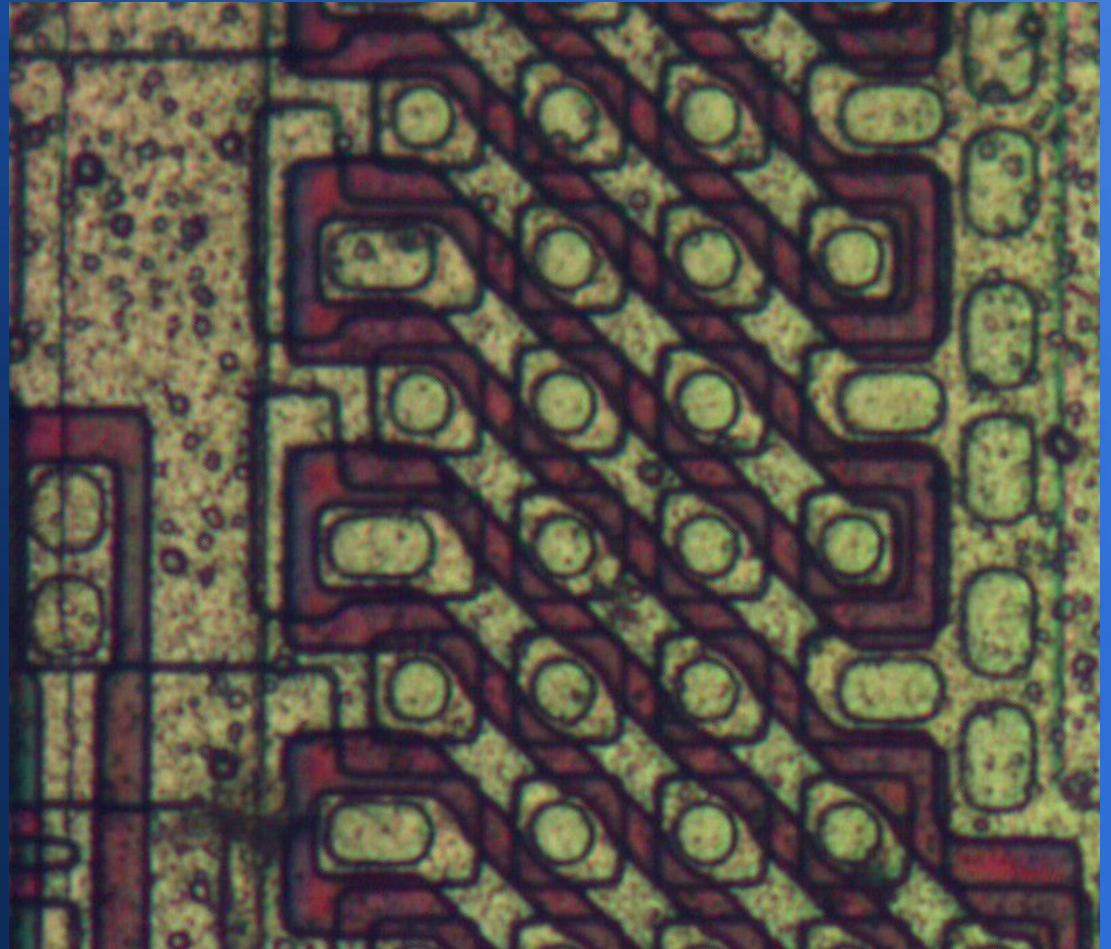
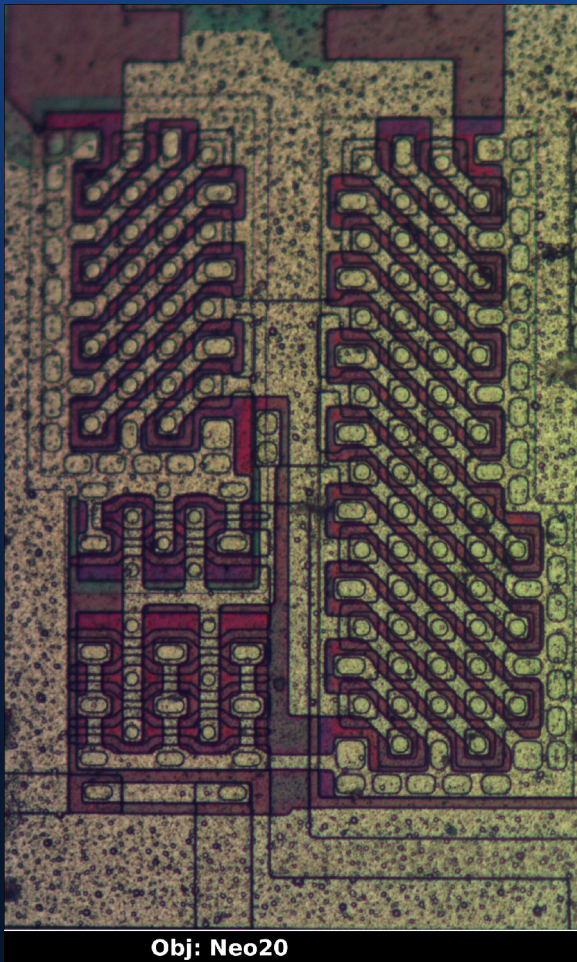
Actual small-signal NMOS



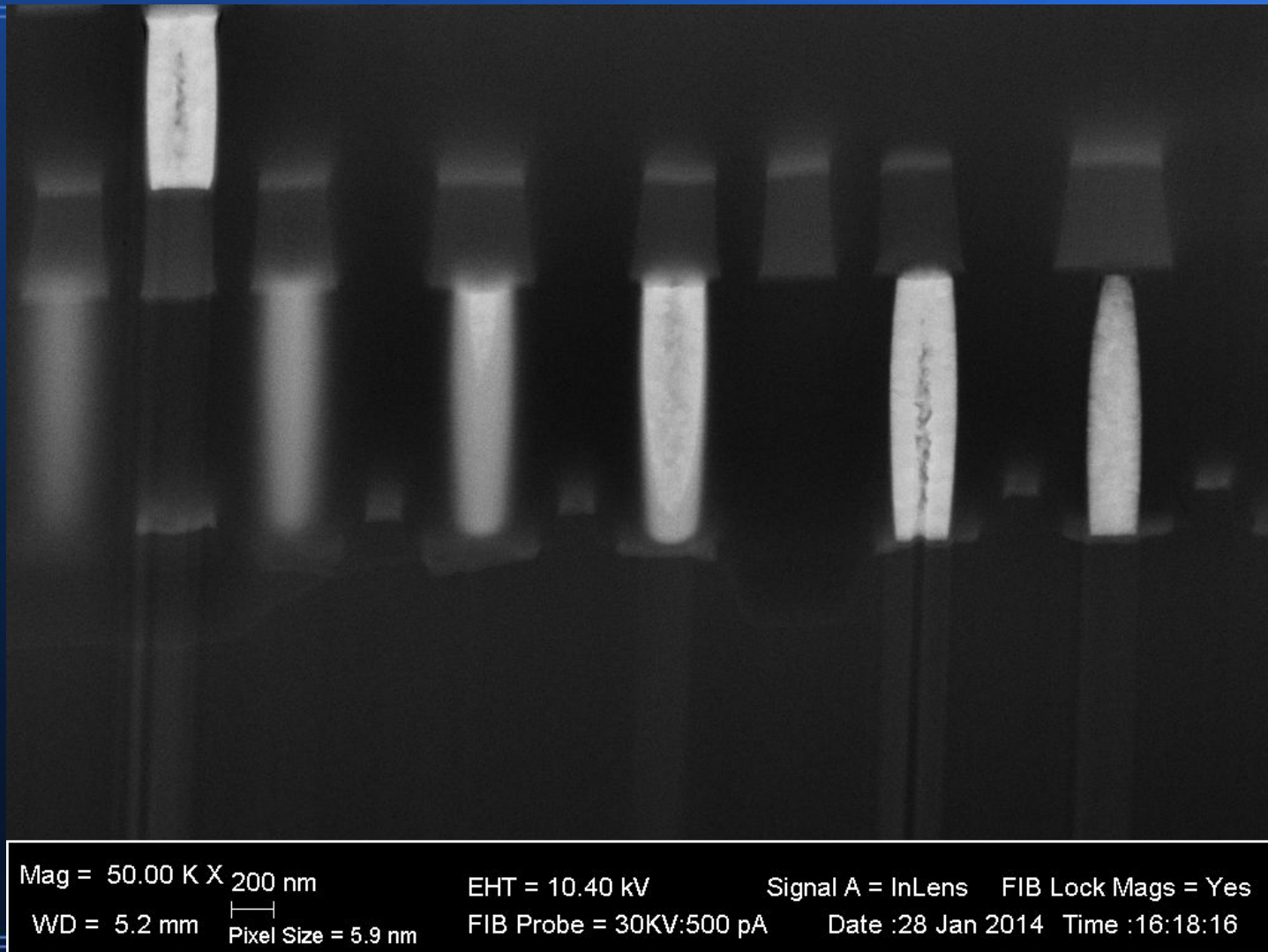
Dopant stain of two PMOS



Actual pad-driver MOSFETs



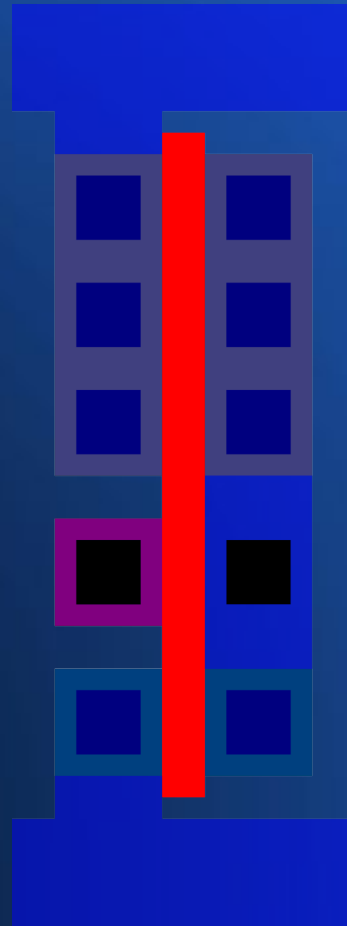
MOSFET cross section



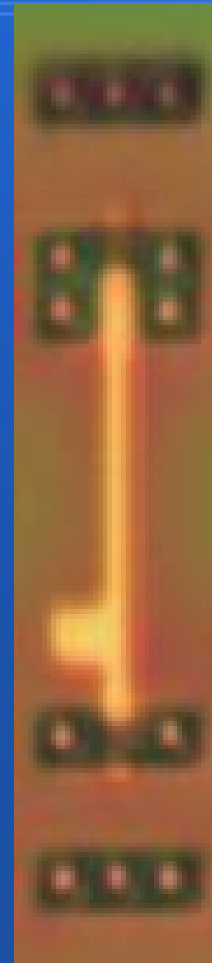
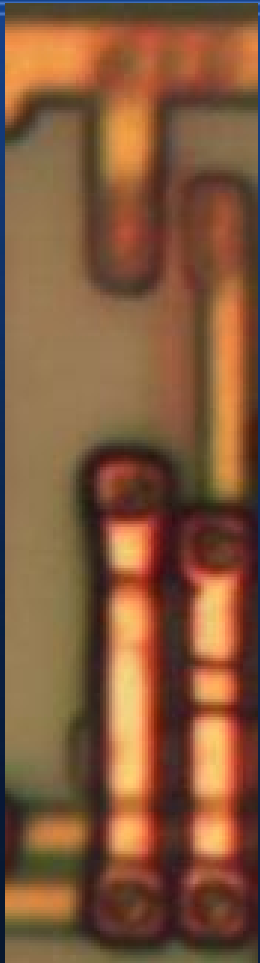
Transistor sizing

- Lots of tricks needed to get good performance
- $R_{ds(on)}$ of PMOS is $\sim 2.5\times$ NMOS
- Channel width increased to compensate

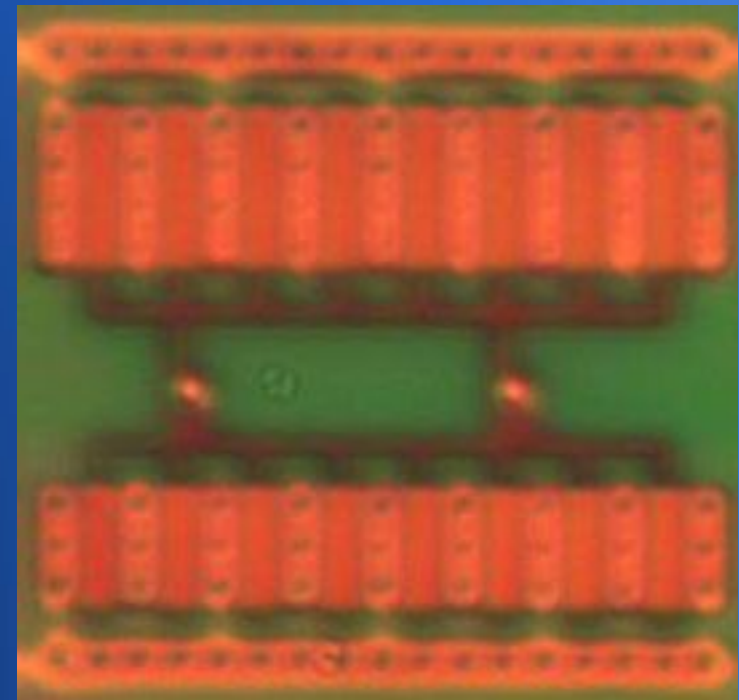
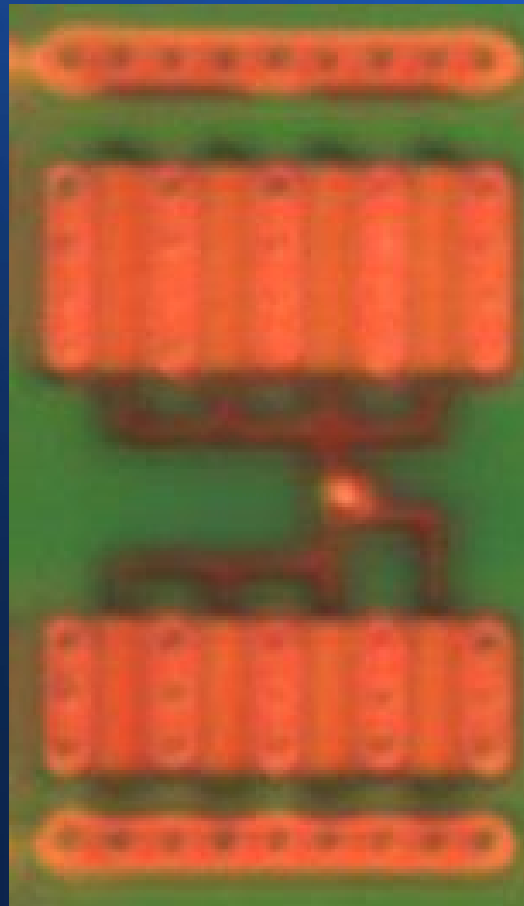
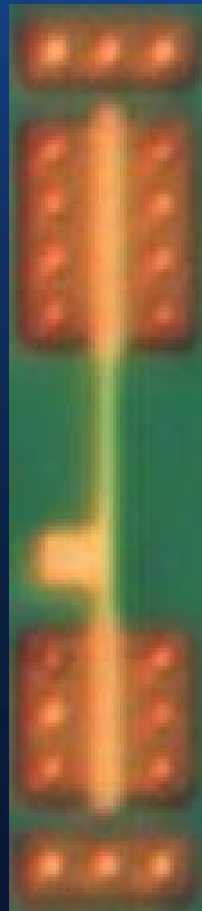
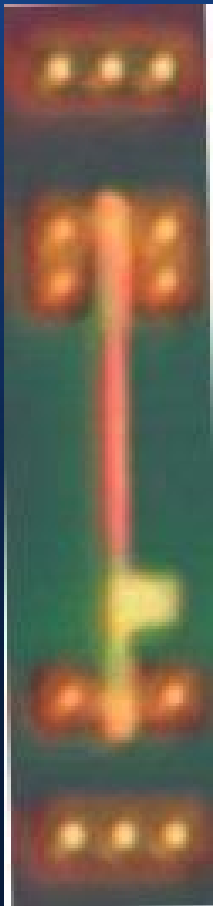
Putting it all together: Inverter



Actual inverter: SID600



Varying drive strength

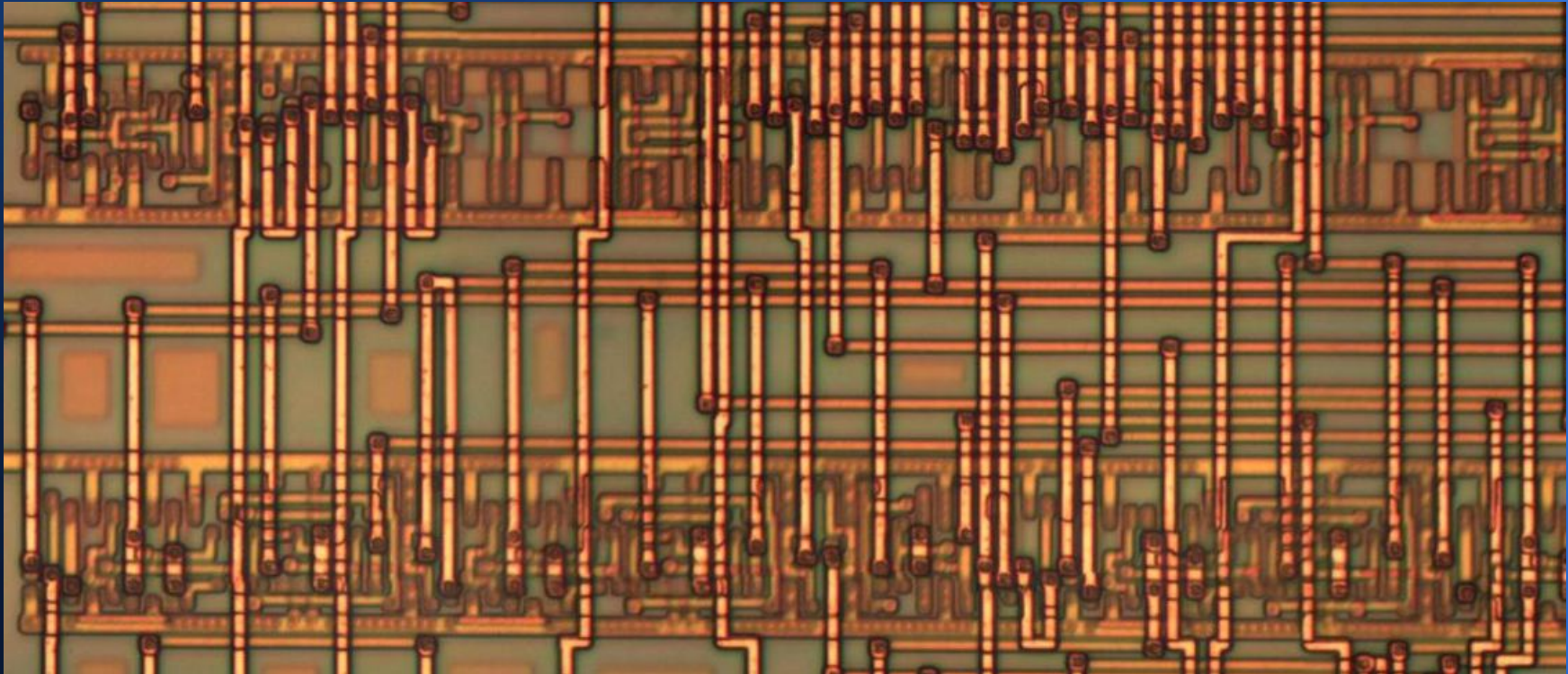


Standard cells



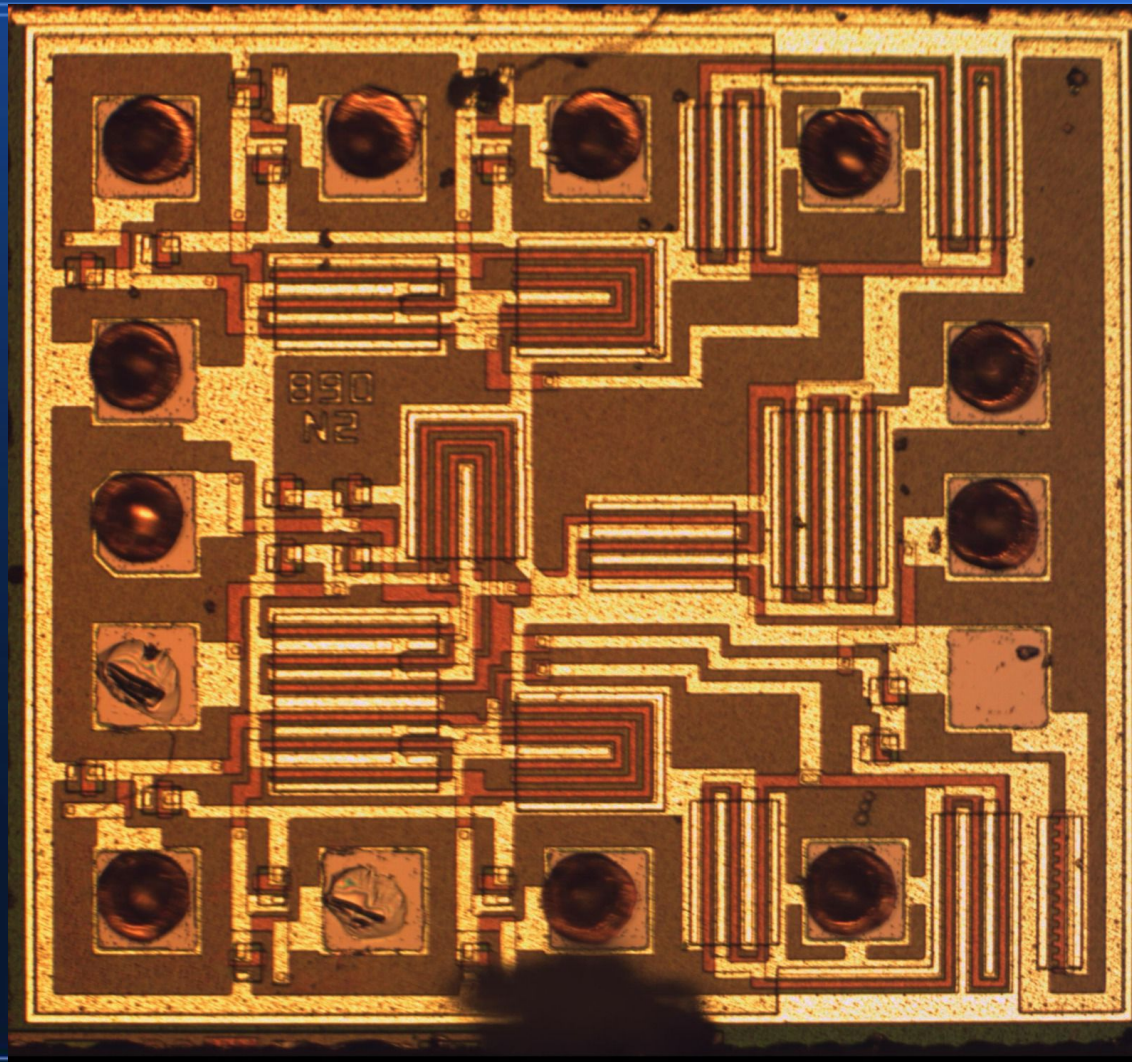
Standard cell routing

- Layers typically alternate X and Y axes

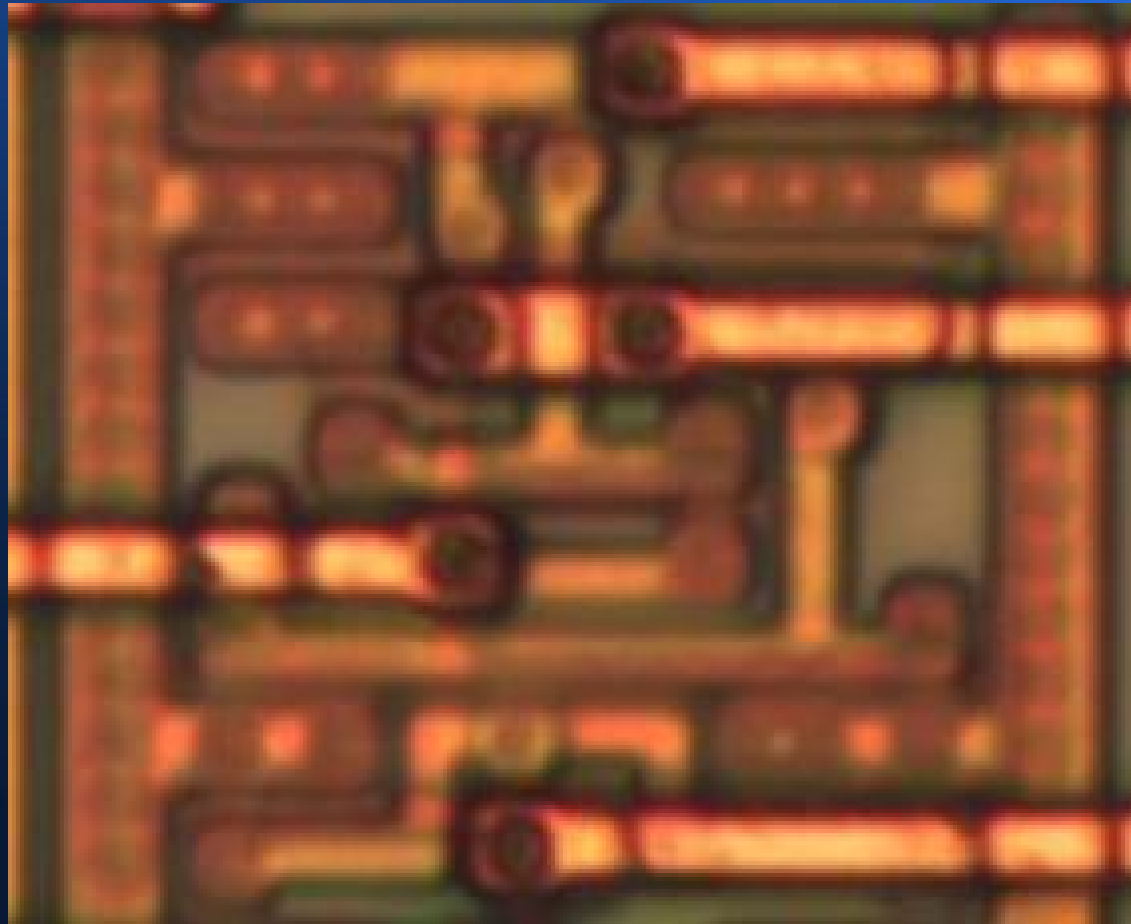


- Demo of vectorization

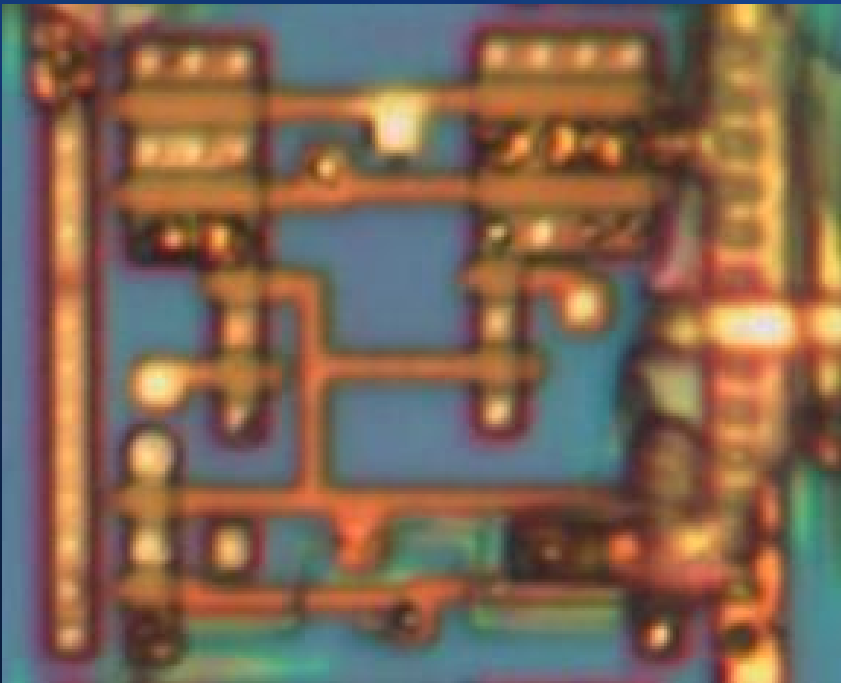
In-class exercise 1



In-class exercise 2: Metal



In class exercise 2: Poly



In class exercise 2: Active



Questions?

- TA: Andrew Zonenberg <azonenberg@drawersteak.com>
- Image credit: Some images CC-BY from:
 - John McMaster <JohnDMcMaster@gmail.com>

